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Summary of Claimed Subject Matter

Claimed embodiments of the invention provide a method for processing a substrate comprising depositing an amorphous carbon layer on the substrate (p.6, paragraph [0020], lines 3-4).

In the embodiments of claim 1, a method for processing a substrate in a processing chamber comprises positioning the substrate in a processing chamber (p. 6-7, paragraph [0021], lines 1-8), introducing a processing gas into the processing chamber wherein the processing gas comprises one or more hydrocarbon compounds without containing silicon and an argon carrier gas (p.7-8, paragraph [0024], line 1 – [0025], line 10), generating a plasma of the processing gas by applying power from a dual-frequency RF source (p.8, paragraph [0026], lines 1-11; p.8, paragraph [0027], lines 1-2), and depositing an amorphous carbon layer consisting essentially of hydrogen and carbon on the substrate (p.15, paragraph [0052], lines 1-2, Figure 2A, item 230; p.7, paragraph [0022], lines 1-7).

In the embodiments of claim 9, a method for processing a substrate in a processing chamber comprises forming a dielectric material layer on a surface of the substrate (p.15, paragraph [0051], line 1, Figure 2A, item 220), depositing one or more amorphous carbon layers consisting essentially of hydrogen and carbon on the dielectric material layer (p.15, paragraph [0052], lines 1-2, Figure 2A, item 230; p.7, paragraph [0022], lines 1-7) by a process comprising introducing a processing gas comprising one or more hydrocarbon compounds without containing silicon and an argon carrier gas (p.7-8, paragraph [0024], line 1 – [0025], line 10), generating a plasma of the processing gas by applying power from a dual-frequency RF source (p.8, paragraph [0026], lines 1-11; p.8, paragraph [0027], lines 1-2), etching the one or more amorphous carbon layers to form a patterned amorphous carbon layer (p.17, paragraph [0058], lines 3-5, Figure 2B), and etching feature definitions in the dielectric material layer corresponding to the patterned one or more amorphous carbon layers (p.17, paragraph [0059], lines 1-3, Figure 2C).

In the embodiments of claim 22, a method for processing a substrate comprises depositing one or more dielectric layers on a substrate surface (p.15, paragraph [0050],

lines 1-3, Figure 2A, item 210; p.15, paragraph [0051], line 1, Figure 2A, item 220), wherein the one or more dielectric layers comprise silicon, oxygen, and carbon and has a dielectric constant of about 3 or less (p. 15, paragraph [0050], lines 4-6, Figure 2A, item 210), forming one or more amorphous carbon layers consisting essentially of hydrogen and carbon on the one or more dielectric layers (p.15, paragraph [0052], lines 1-2, Figure 2A, item 230; p.7, paragraph [0022], lines 1-7) by a process comprising introducing a processing gas comprising one or more hydrocarbon compounds without containing silicon and an argon carrier gas (p.7-8, paragraph [0024], line 1 – [0025], line 10), generating a plasma of the processing gas by applying power from a dual-frequency RF source (p.8, paragraph [0026], lines 1-11; p.8, paragraph [0027], lines 1-2), defining a pattern in at least one region of the one or more amorphous carbon layers (p.17, paragraph [0058], lines 3-5, Figure 2B), forming feature definitions in the one or more dielectric layers by the pattern formed in the at least one region of the one or more amorphous carbon layers (p.17, paragraph [0059], lines 1-3, Figure 2C), and depositing one or more conductive materials in the feature definitions (p.18, paragraph [0061], lines 1-2, Figure 2E, item 260).

COMMENTS

In response to the Notice of Non-Compliant Appeal Brief mailed April 30, 2007, Appellants submit the above corrected Summary of Claimed Subject Matter. In the Summary of Claimed Subject Matter, Appellants summarize the independent claims 1, 9, and 22 pending in the application rather than summarize claims 11, 17, 24, 26, and 27 as was presented in the Appeal Brief filed March 9, 2007.

According to M.P.E.P. § 1205.03 (b), "When the Office holds the brief to be defective solely due to appellant's failure to provide a summary of the claimed subject matter as required by 37 CFR 41.37(c)(1)(v), an entire new brief need not, and should not, be filed. Rather, a paper providing a summary of the claimed subject matter as required by 37 CFR 41.37(c)(1)(v) will suffice." Thus, Appellants submit the above Summary of the Claimed Subject Matter.

Appellants respectfully reiterate that the final rejection of claims 11, 17, 18, 20, 24, 26, 27, 34, and 37 is appealed. The Examiner errs in finding that *Huang et al.* anticipates claims 11, 17, 18, 20, 24, 26, 27, 34, and 37. It is respectfully requested that the Examiner's rejections be reversed.

Respectfully submitted,



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